

### General Description

- Latest Trench Power AlphaMOS (αMOS LV) technology
- Integrated Schottky Diode (SRFET) on Low-Side
- Very Low RDS(on) at 4.5V<sub>GS</sub>
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

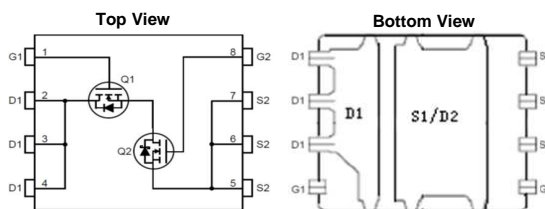
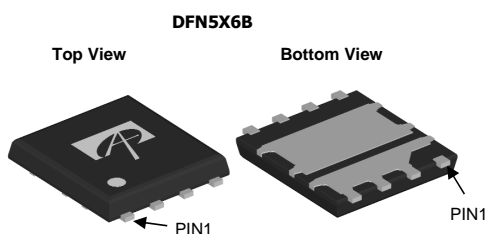
### Application

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

### Product Summary

	Q1	Q2
V <sub>DS</sub>	30V	30V
I <sub>D</sub> (at V <sub>GS</sub> =10V)	28A	32A
R <sub>DS(ON)</sub> (at V <sub>GS</sub> =10V)	<5.2mΩ	<3.9mΩ
R <sub>DS(ON)</sub> (at V <sub>GS</sub> =4.5V)	<9.5mΩ	<6.4mΩ

100% UIS Tested  
 100% R<sub>g</sub> Tested



Q2: SRFET™  
 Soft Recovery MOSFET:  
 Integrated Schottky Diode

### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Parameter	Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage	V <sub>DS</sub>	30		V
Gate-Source Voltage	V <sub>GS</sub>	±20	±20	V
Continuous Drain Current <sup>G</sup>	I <sub>D</sub>	T <sub>C</sub> =25°C	28	A
		T <sub>C</sub> =100°C	22	
Pulsed Drain Current <sup>C</sup>	I <sub>DM</sub>	112	144	
Continuous Drain Current	I <sub>DSM</sub>	T <sub>A</sub> =25°C	22	A
		T <sub>A</sub> =70°C	17	
Avalanche Current <sup>C</sup>	I <sub>AS</sub>	32	50	A
Avalanche Energy L=0.05mH <sup>C</sup>	E <sub>AS</sub>	26	63	mJ
V <sub>DS</sub> Spike	V <sub>SPIKE</sub>	36	36	V
Power Dissipation <sup>B</sup>	P <sub>D</sub>	T <sub>C</sub> =25°C	31	W
		T <sub>C</sub> =100°C	12	
Power Dissipation <sup>A</sup>	P <sub>DSM</sub>	T <sub>A</sub> =25°C	3.6	W
		T <sub>A</sub> =70°C	2.3	
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150		°C

### Thermal Characteristics

Parameter	Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient <sup>A</sup>	R <sub>θJA</sub>	t ≤ 10s	29	24	35	29
Maximum Junction-to-Ambient <sup>A,D</sup>		Steady-State	56	50	67	60
Maximum Junction-to-Case	R <sub>θJC</sub>	3.3	3	4	3.8	°C/W

**Q1 Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.4	1.8	2.2	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A T <sub>J</sub> =125°C		4.3	5.2	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		6	7.2	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		91		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.7	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current <sup>G</sup>				28	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance			1037		pF
C <sub>oss</sub>	Output Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		441		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			61		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.7	1.5	2.3	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		15.5	22	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			6.8	10	nC
Q <sub>gs</sub>	Gate Source Charge			3.0		nC
Q <sub>gd</sub>	Gate Drain Charge			3.6		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		5.5		ns
t <sub>r</sub>	Turn-On Rise Time			3.3		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			18		ns
t <sub>f</sub>	Turn-Off Fall Time			4.3		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, dI/dt=500A/μs		12.7		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, dI/dt=500A/μs		17.2		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

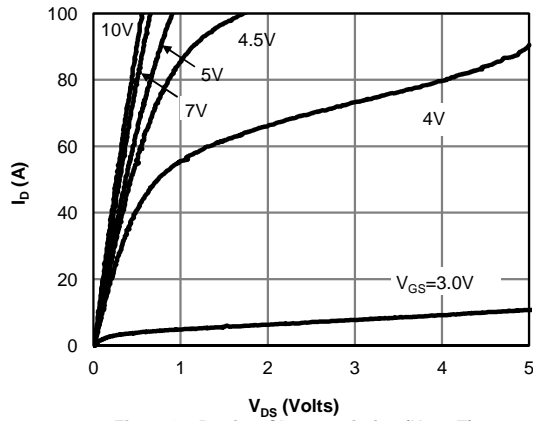
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by package.

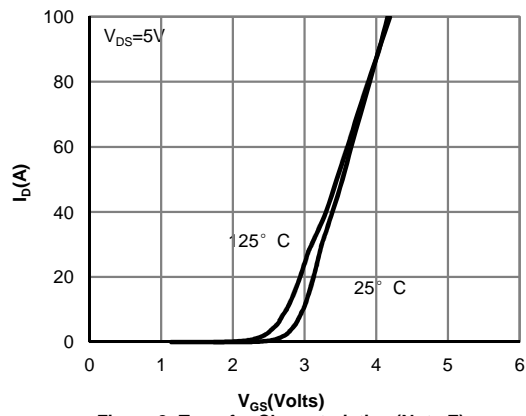
H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

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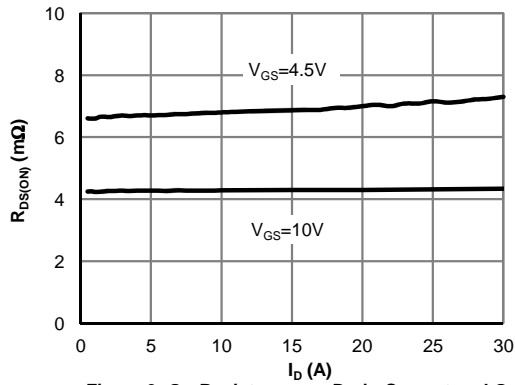
**Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



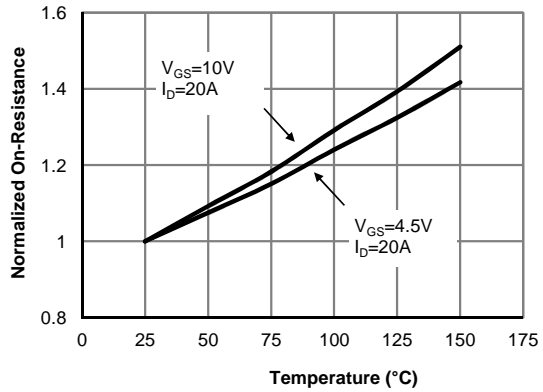
**Figure 1: On-Region Characteristics (Note E)**



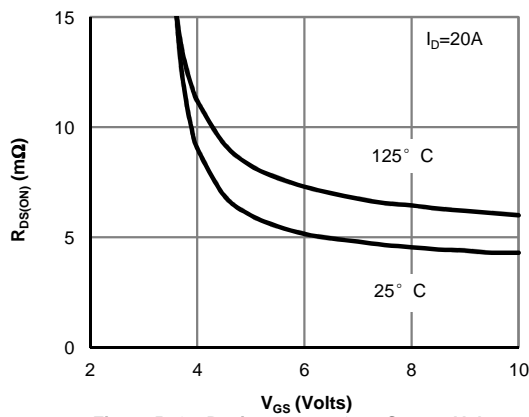
**Figure 2: Transfer Characteristics (Note E)**



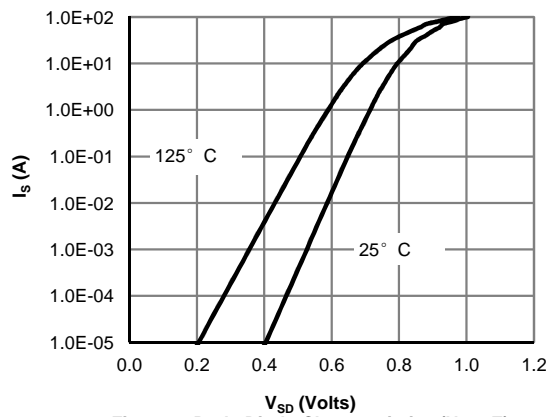
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

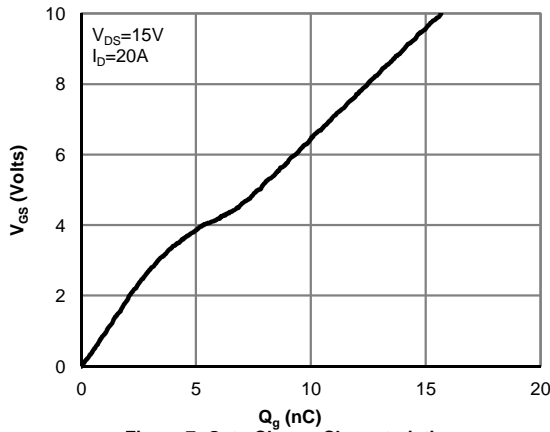


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

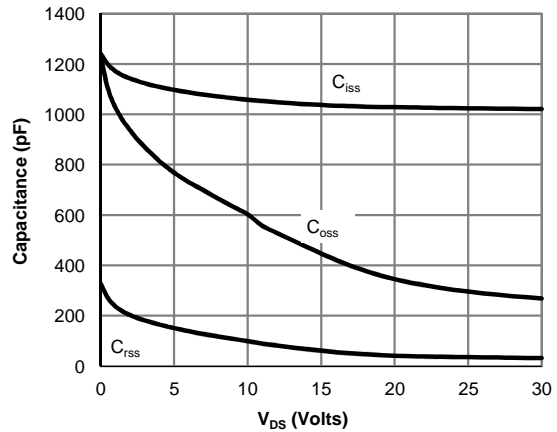


**Figure 6: Body-Diode Characteristics (Note E)**

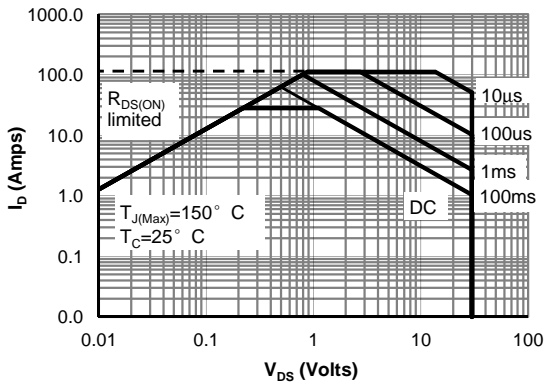
**Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



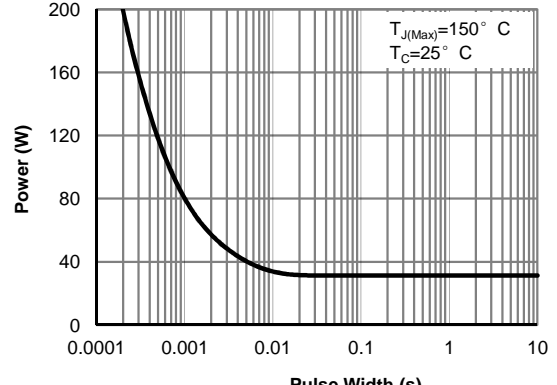
**Figure 7: Gate-Charge Characteristics**



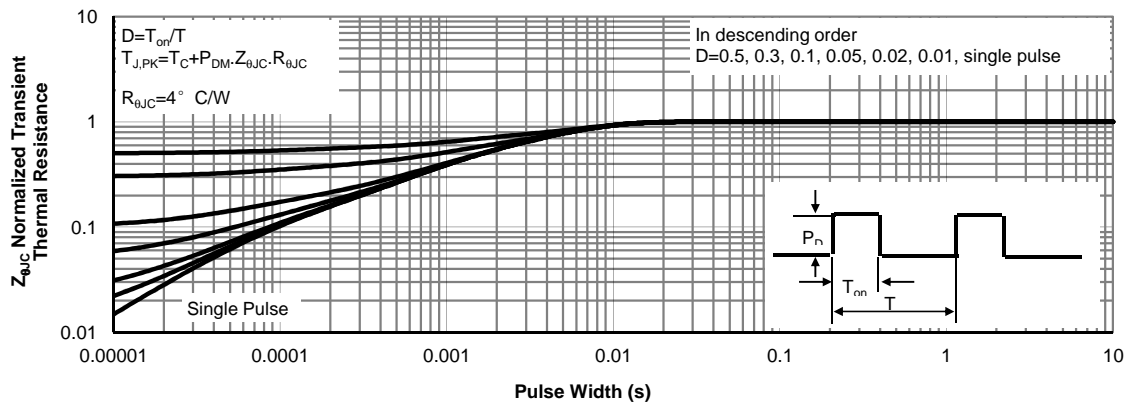
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)**



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

**Q1-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

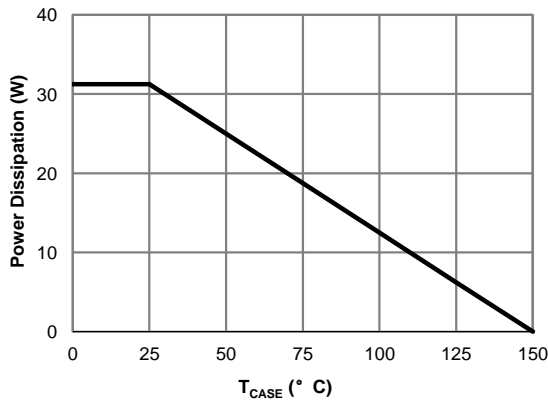


Figure 12: Power De-rating (Note F)

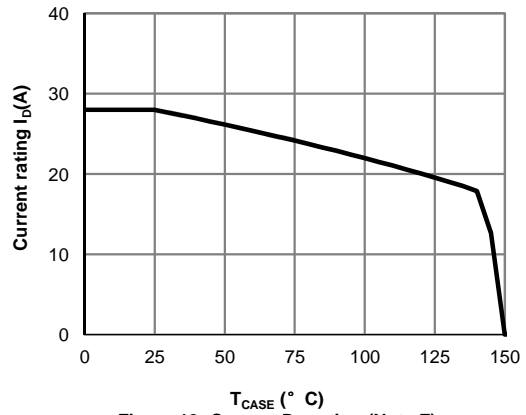


Figure 13: Current De-rating (Note F)

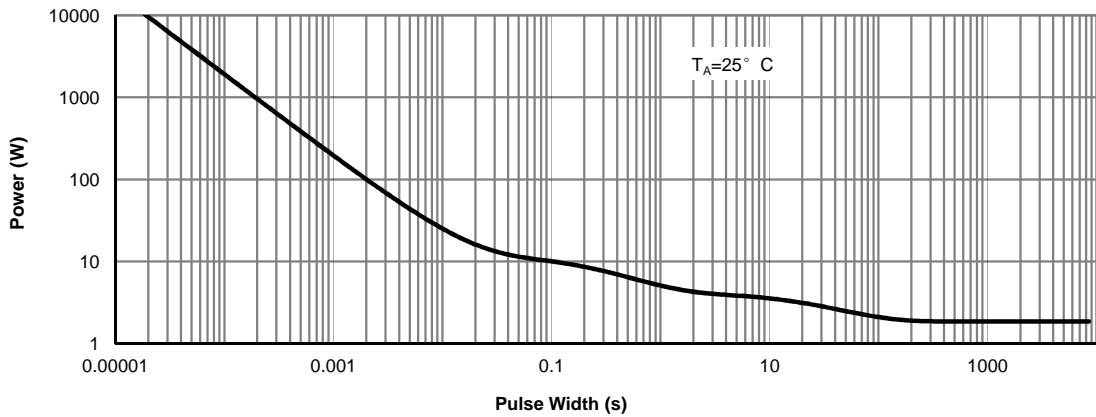


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

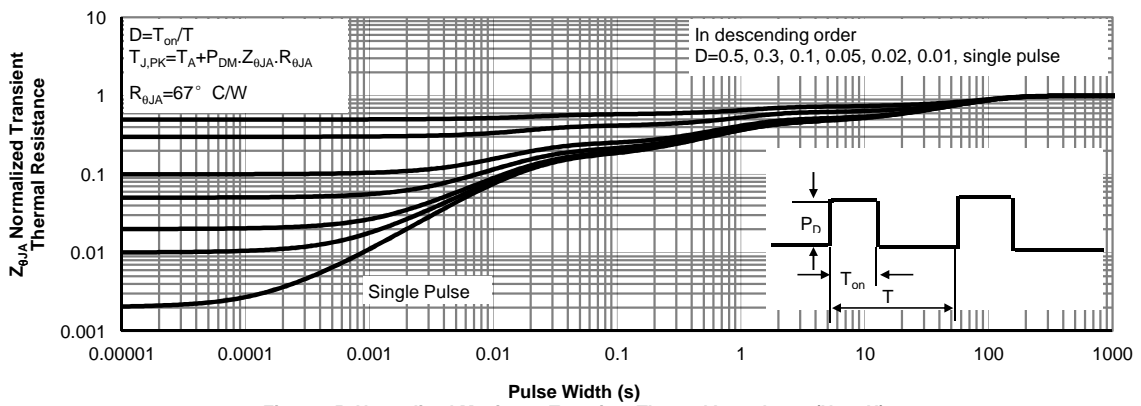


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

**Q2 Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =10mA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			0.5 100	mA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.4	1.8	2.2	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A T <sub>J</sub> =125°C		3.1 4.2	3.9 5.3	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		4.8	6.4	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		85		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.48	0.6	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current <sup>G</sup>				36	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance			1975		pF
C <sub>oss</sub>	Output Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		913		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			92		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.7	1.5	2.3	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		29	40	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge			13.6	19	nC
Q <sub>gs</sub>	Gate Source Charge			5.8		nC
Q <sub>gd</sub>	Gate Drain Charge			5.3		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		7.9		ns
t <sub>r</sub>	Turn-On Rise Time			4.0		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			27.3		ns
t <sub>f</sub>	Turn-Off Fall Time			6.5		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, dI/dt=500A/μs		19		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, dI/dt=500A/μs		36.7		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

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G. The maximum current rating is limited by package.

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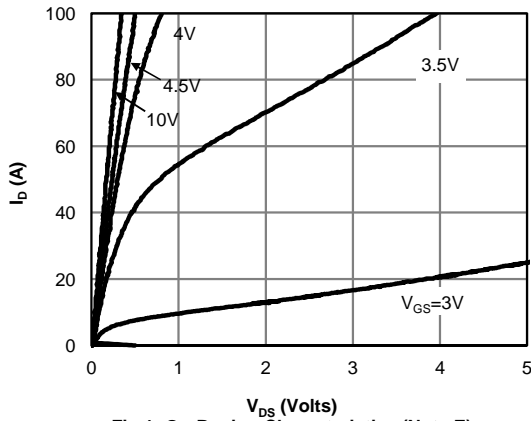


Fig 1: On-Region Characteristics (Note E)

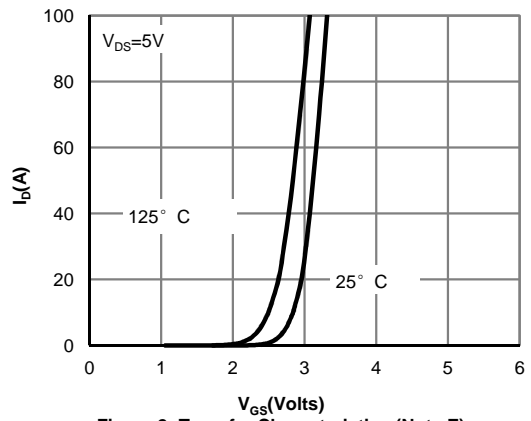


Figure 2: Transfer Characteristics (Note E)

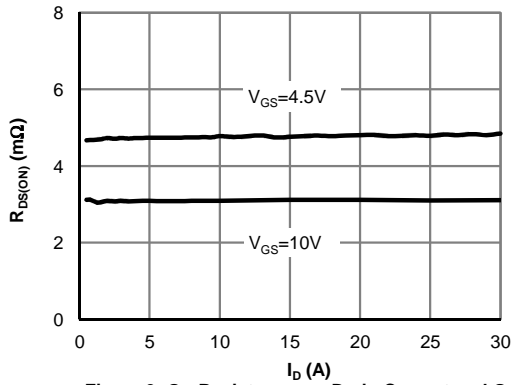


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

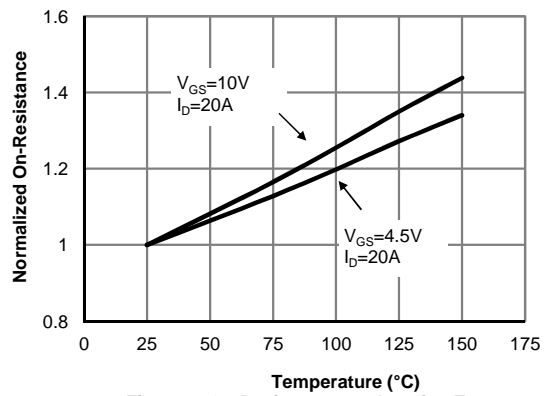


Figure 4: On-Resistance vs. Junction Temperature (Note E)

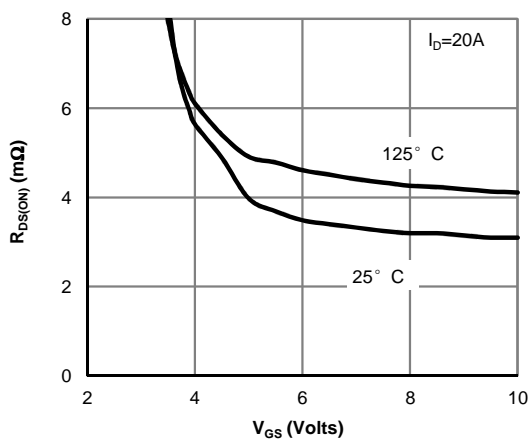


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

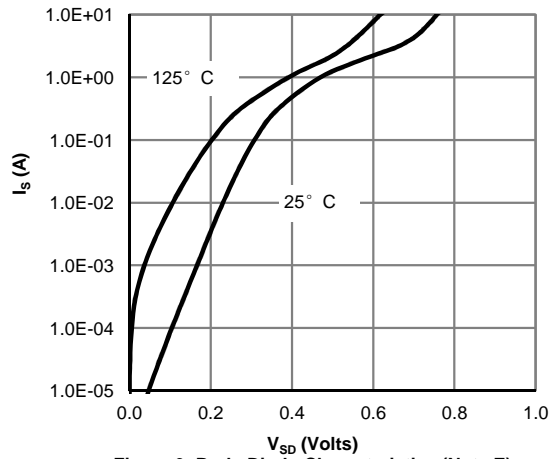


Figure 6: Body-Diode Characteristics (Note E)

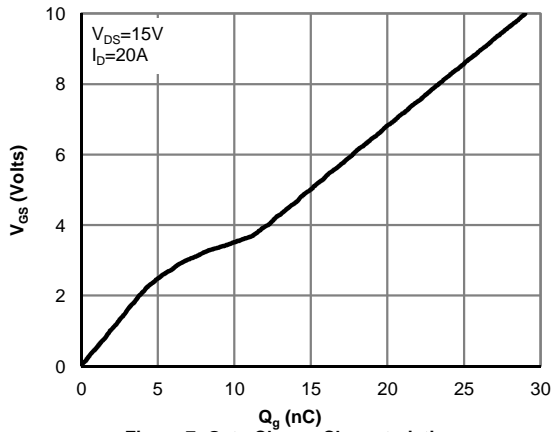


Figure 7: Gate-Charge Characteristics

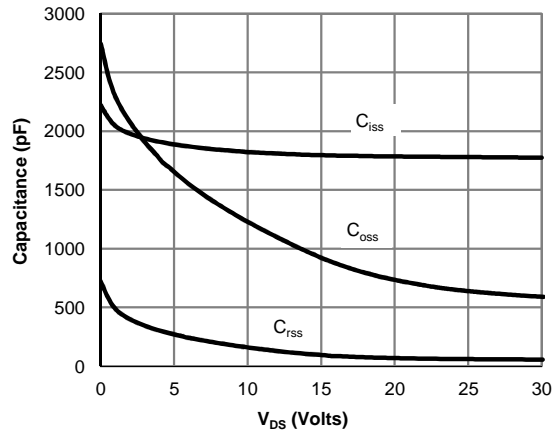


Figure 8: Capacitance Characteristics

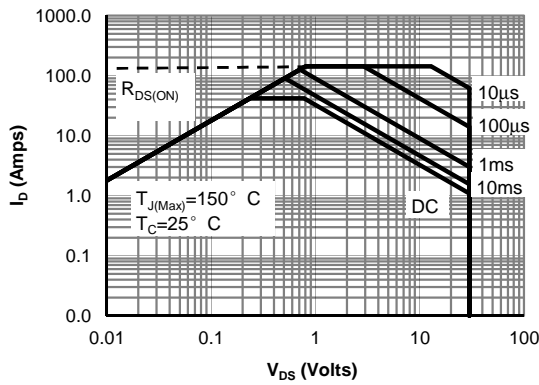


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

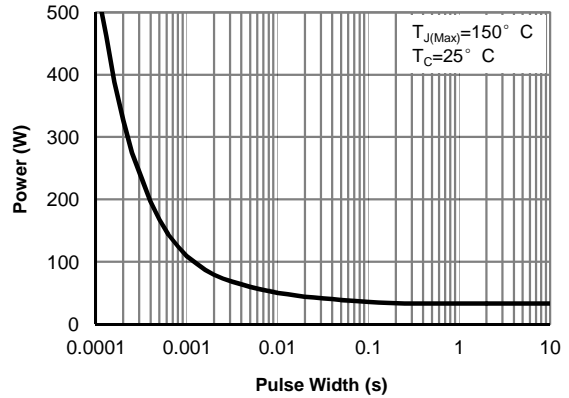


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

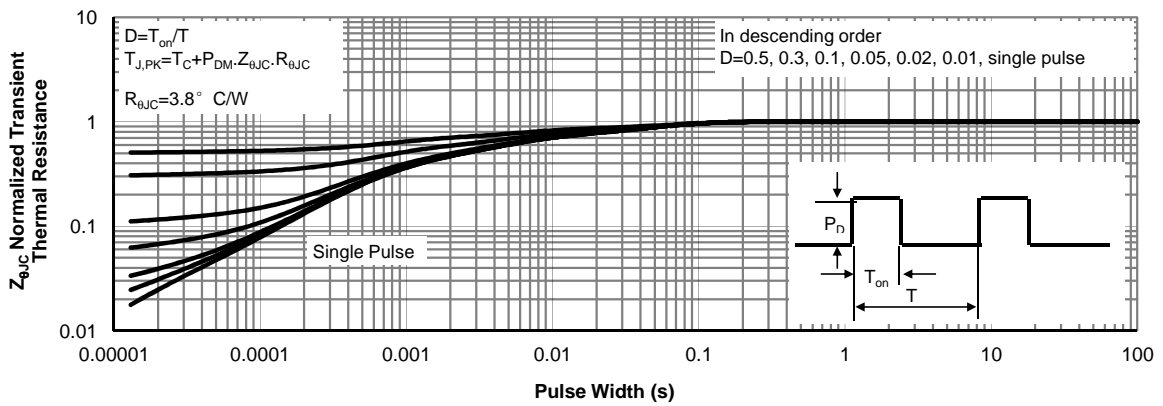


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)



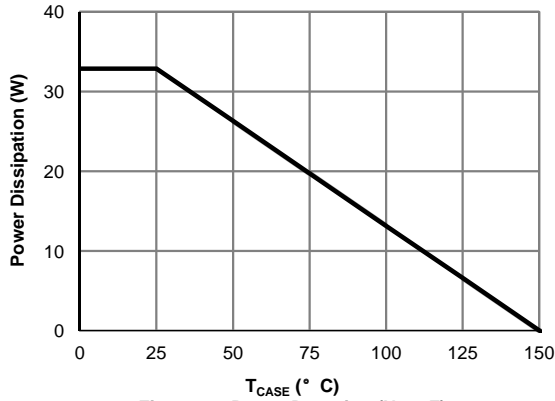


Figure 12: Power De-rating (Note F)

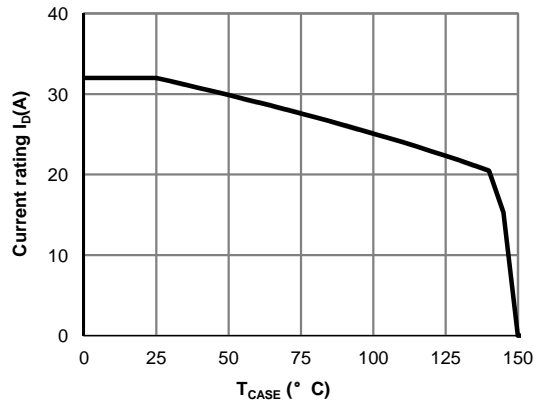


Figure 13: Current De-rating (Note F)

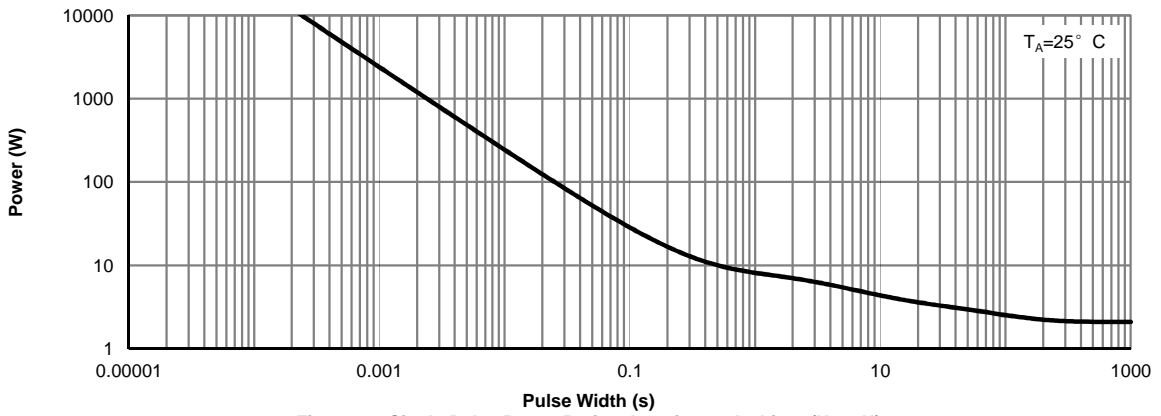


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

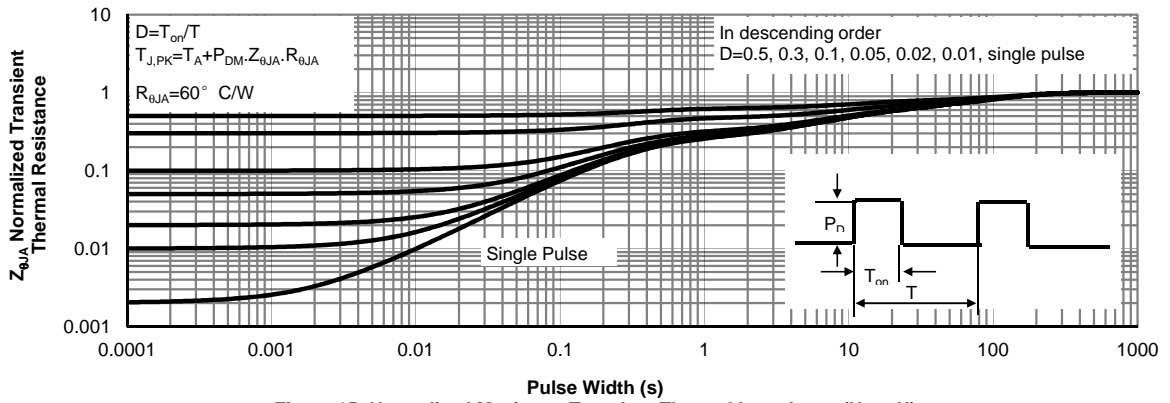
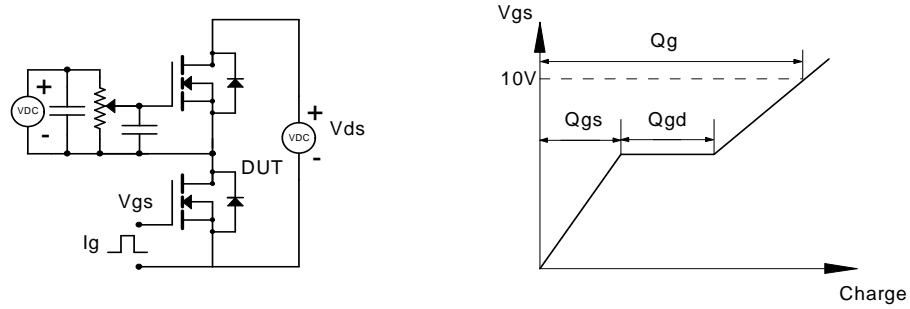
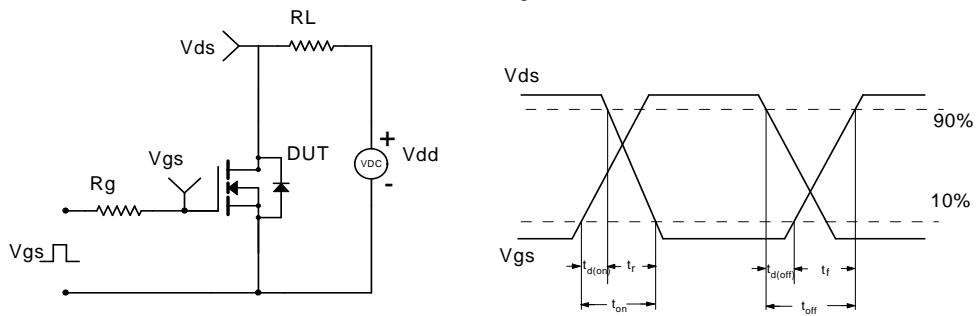


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

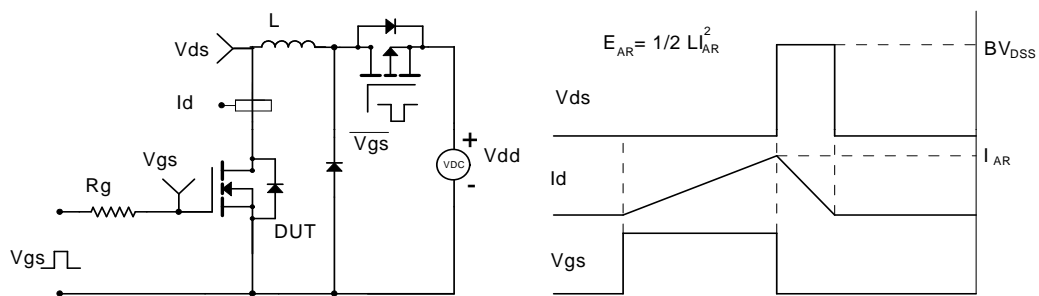
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

